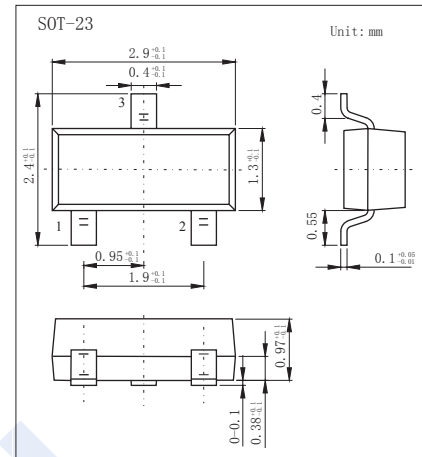
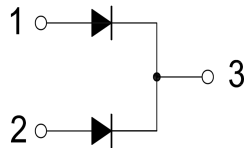


Schottky Diodes

RB425D (KB425D)

■ Features

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	V _{RM}	40	V
DC Blocking Voltage	V _R	40	
Average Rectified Output Current	I _o	0.1	A
Peak Forward Surge Current	I _{FM}	1	
Power Dissipation	P _D	250	mW
Thermal Resistance Junction to Ambient	R _{θJA}	400	°C/W
Junction Temperature	T _J	125	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V _R	I _R = 100 uA	40			V
Forward voltage	V _F	I _F = 10mA			0.34	
		I _F = 100mA			0.55	
Reverse voltage leakage current	I _R	V _R =10 V			30	uA
Capacitance between terminals	C _T	V _R =10 V, f= 1 MHz		6		pF

■ Marking

Marking	D3L
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Schottky Diodes

RB425D (KB425D)

■ Typical Characteristics

